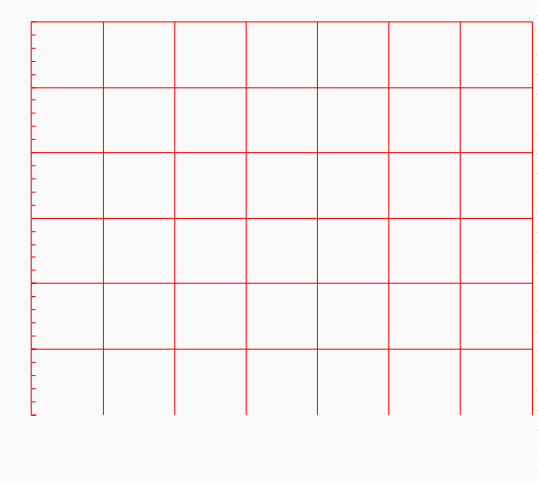
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	3.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	20	mA
				35	
I_H	I_T =100mA		MAX.	20	mA
dV/dt	V_D=540V Gate Open T_j =125		MIN.	500	

Maximum power dissipation versus RMS on-state current



RMS on-state current versus case temperature

FIG.7　Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



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